



IXTQ120N20P Information

Part Number IXTQ120N20P

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 200V 120A TO-3P

Package TO-3P-3, SC-65-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

For Reference Only

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXTQ120N20P Specifications

Manufacturer Part Number IXTQ120N20P Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-3P-3, SC-65-3 Series PolarHT? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 120A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 152nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 6000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 714W (Tc) Rds On (Max) @ Id, Vgs 22 mOhm @ 500mA, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P-3, SC-65-3 Package / Case TO-3P-3, SC-65-3		
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C120A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds6000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)714W (Tc)Rds On (Max) @ Id, Vgs22 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Series	PolarHT?
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Current - Continuous Drain (Id) @ 25°C120A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds6000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)714W (Tc)Rds On (Max) @ Id, Vgs22 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs152nC @ 10VInput Capacitance (Ciss) (Max) @ Vds6000pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)714W (Tc)Rds On (Max) @ Id, Vgs22 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Drain to Source Voltage (Vdss)	200V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 6000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 714W (Tc) Rds On (Max) @ Id, Vgs 22 mOhm @ 500mA, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Current - Continuous Drain (Id) @ 25°C	120A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 6000pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 22 mOhm @ 500mA, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 22 mOhm @ 500mA, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)714W (Tc)Rds On (Max) @ Id, Vgs22 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	Gate Charge (Qg) (Max) @ Vgs	152nC @ 10V
FET Feature - To-3P-3, SC-65-3	Input Capacitance (Ciss) (Max) @ Vds	6000pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 22 mOhm @ 500mA, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs22 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-3PPackage / CaseTO-3P-3, SC-65-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Power Dissipation (Max)	714W (Tc)
Mounting Type Through Hole Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Rds On (Max) @ Id, Vgs	22 mOhm @ 500mA, 10V
Supplier Device Package TO-3P Package / Case TO-3P-3, SC-65-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-3P-3, SC-65-3	Mounting Type	Through Hole
	Supplier Device Package	TO-3P
Report errors?	Package / Case	TO-3P-3, SC-65-3
		Report errors?

IXTQ120N20P Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTQ120N20P Payment Methods



















IXTQ120N20P Shipping Methods













If you have any question about IXTQ120N20P, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com